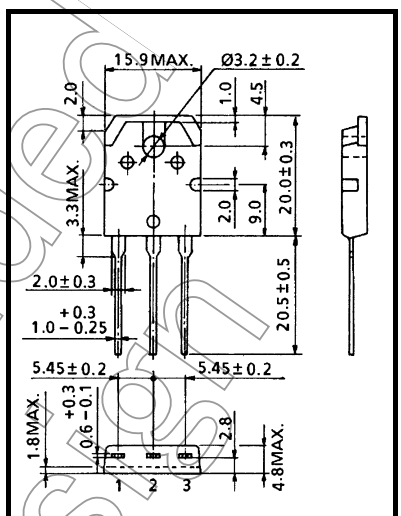
TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SC5197

Power Amplifier Applications

- Complementary to 2SA1940
- Suitable for use in 55-W high fidelity audio amplifier's output stage

Unit: mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	—
JEITA	—
TOSHIBA	2-16C1A

Weight: 4.7 g (typ.)

Absolute Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	8	A
Base current	I_B	0.8	A
Collector power dissipation (Tc = 25°C)	P_C	80	W
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55 to 150	°C

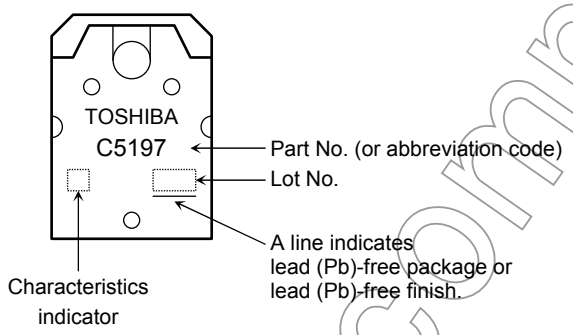
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Tc = 25°C)

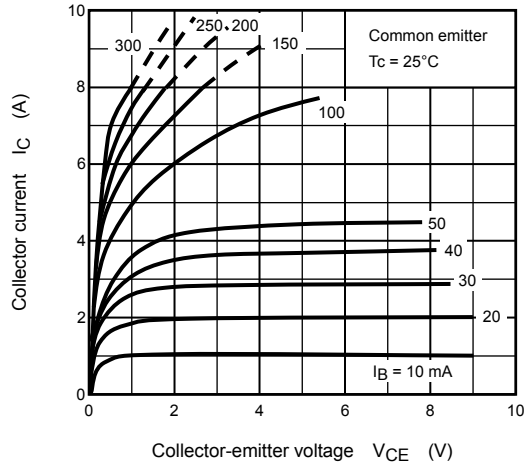
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 120 V, I_E = 0	—	—	5.0	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 5 V, I_C = 0	—	—	5.0	μA
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = 50 mA, I_B = 0	120	—	—	V
DC current gain	$h_{FE\ (1)}$ (Note)	V_{CE} = 5 V, I_C = 1 A	55	—	160	
	$h_{FE\ (2)}$	V_{CE} = 5 V, I_C = 4 A	35	75	—	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 6 A, I_B = 0.6 A	—	0.35	2.0	V
Base-emitter voltage	V_{BE}	V_{CE} = 5 V, I_C = 4 A	—	0.95	1.5	V
Transition frequency	f_T	V_{CE} = 5 V, I_C = 1 A	—	30	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	120	—	pF

Note: $h_{FE\ (1)}$ classification R: 55 to 110, O: 80 to 160

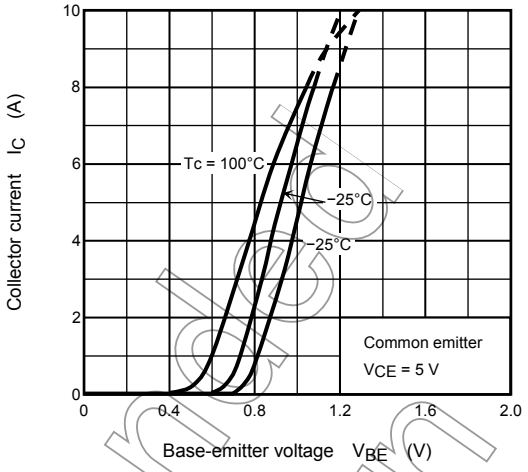
Marking



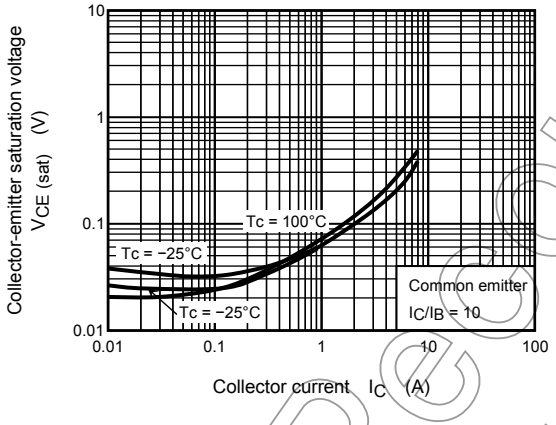
$I_C - V_{CE}$



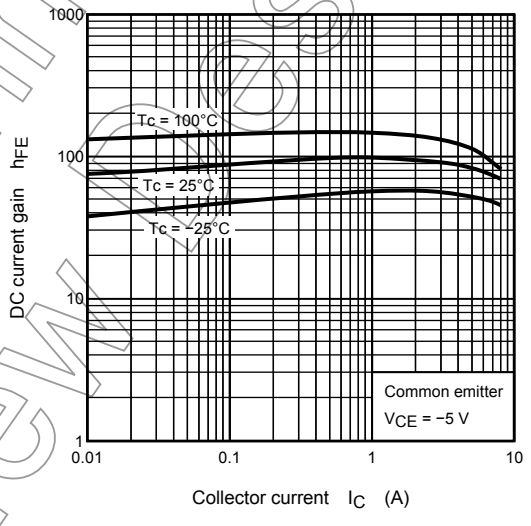
$I_C - V_{BE}$



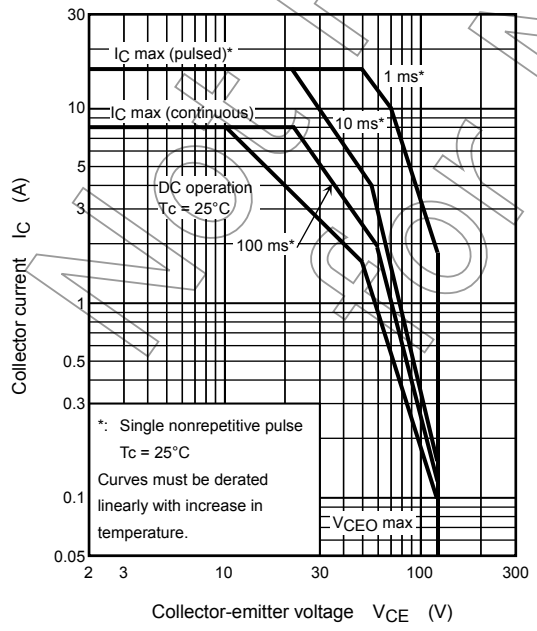
$V_{CE\ (sat)} - I_C$



$h_{FE} - I_C$



Safe Operating Area



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